



STA6620

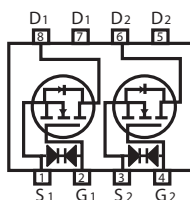
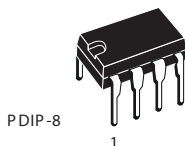
Dual N-Channel Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY

V _{DSS}	I _D	R _{DS(ON)} (m Ω) Max
40V	7A	25 @ V _{GS} = 10V 42 @ V _{GS} = 4.5V

FEATURES

- Super high dense cell design for low R_{DS(ON)}.
- Rugged and reliable.
- Surface Mount Package.
- ESD Protected.



ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V _{DS}	40	V
Gate-Source Voltage		V _{GS}	±20	V
Drain Current-Continuous ^a @ T _a	25°C	I _D	7	A
	70°C		5.9	A
-Pulsed ^b		I _{DM}	30	A
Drain-Source Diode Forward Current ^a		I _S	1.7	A
Maximum Power Dissipation ^a	T _a = 25°C	P _D	3	W
	T _a = 70°C		2	
Operating Junction and Storage Temperature Range		T _J , T _{STG}	-55 to 150	°C

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient ^a	R θ JA	41.5	°C/W
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STA6620

N-Channel ELECTRICAL CHARACTERISTICS (TA = 25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ ^c	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	40			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =32V, V _{GS} =0V			1	uA
Gate-Body Leakage	I _{GSS}	V _{GS} =±20V, V _{DS} = 0V			±10	nA
ON CHARACTERISTICS ^b						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D = 250uA	1	2	3	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =7A		19	25	m ohm
		V _{GS} =4.5V, I _D = 5A		28	42	m ohm
On-State Drain Current	I _{D(ON)}	V _{DS} = 5V, V _{GS} = 10V	15			A
Forward Transconductance	g _{FS}	V _{DS} = 5V, I _D = 7A		13		S
DYNAMIC CHARACTERISTICS ^c						
Input Capacitance	C _{ISS}	V _{DS} =25V, V _{GS} = 0V f =1.0MHz		710		pF
Output Capacitance	C _{OSS}			110		pF
Reverse Transfer Capacitance	C _{RSS}			68		pF
SWITCHING CHARACTERISTICS ^c						
Turn-On Delay Time	t _{D(ON)}	V _{DD} = 20V I _D = 1 A V _{GS} = 10V R _{GEN} = 3.3 ohm		16.5		ns
Rise Time	t _r			14		ns
Turn-Off Delay Time	t _{D(OFF)}			40		ns
Fall Time	t _f			6.5		ns
Total Gate Charge	Q _g	V _{DS} =20V, I _D =7A,V _{GS} =10V		13.3		nC
		V _{DS} =20V, I _D =7A,V _{GS} =4.5V		6.7		nC
Gate-Source Charge	Q _{gs}	V _{DS} =20V, I _D = 7 A V _{GS} =4.5V		2		nC
Gate-Drain Charge	Q _{gd}			3.7		nC

STA6620

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ ^c	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS ^b						
Diode Forward Voltage	V _{SD}	V _{GS} = 0V, I _S =1.7A		0.8	1.2	V

Notes

- a.Surface Mounted on FR4 Board, t≤10sec.
- b.Pulse Test:Pulse Width≤ 300us, Duty Cycle≤ 2%.
- c.Guaranteed by design, not subject to production testing.

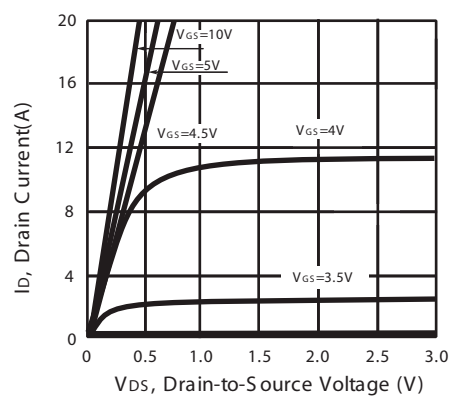


Figure 1. Output Characteristics

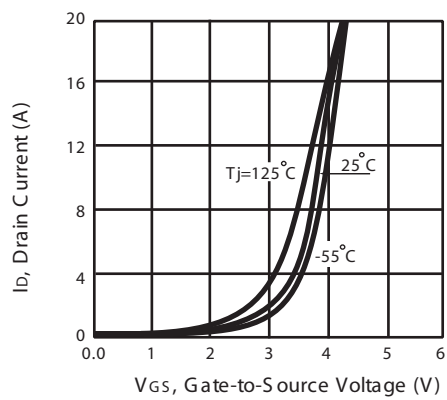


Figure 2. Transfer Characteristics

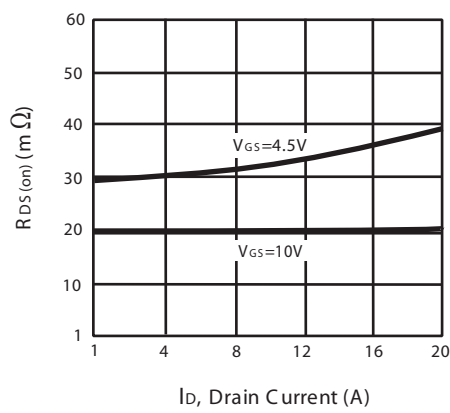


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

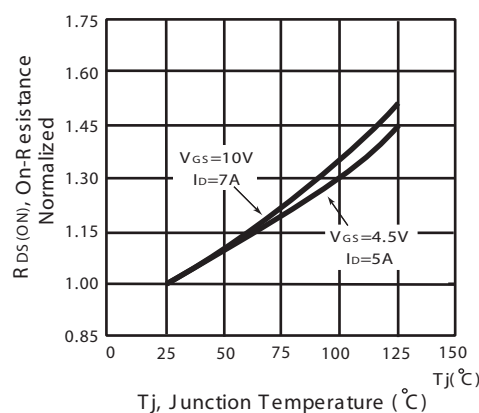


Figure 4. On-Resistance Variation with Drain Current and Temperature

STA6620

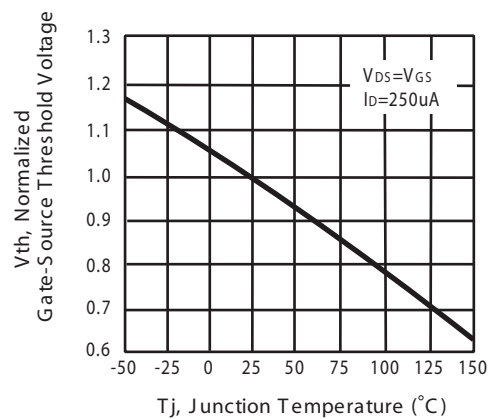


Figure 5. Gate Threshold Variation with Temperature

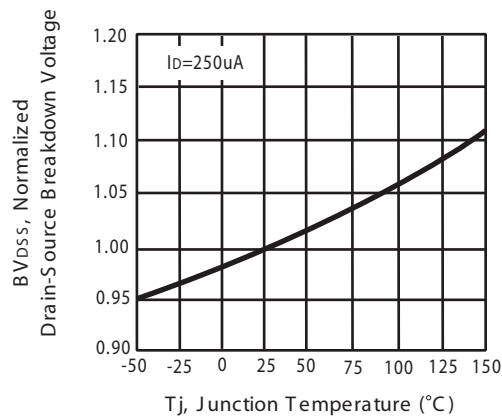


Figure 6. Breakdown Voltage Variation with Temperature

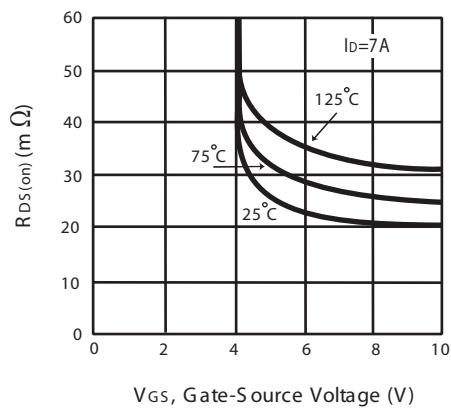


Figure 7. On-Resistance vs. Gate-Source Voltage

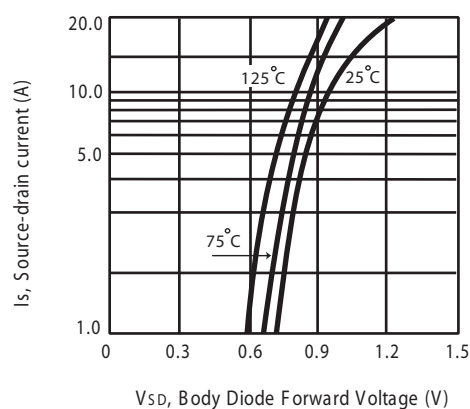


Figure 8. Body Diode Forward Voltage Variation with Source Current

STA6620

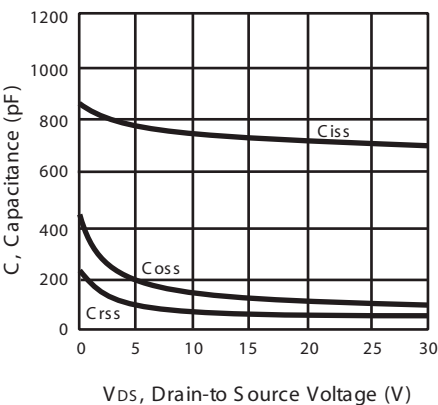


Figure 9. Capacitance

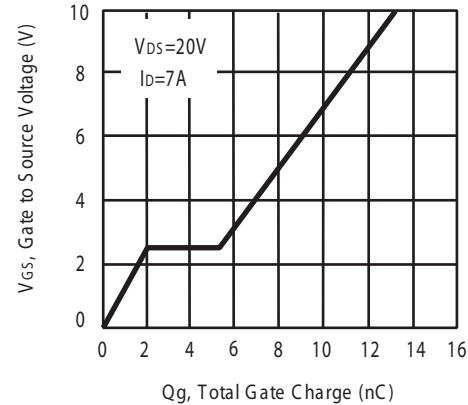


Figure 10. Gate Charge

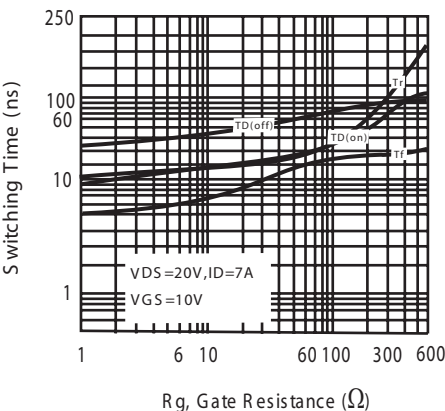


Figure 11.switching characteristics

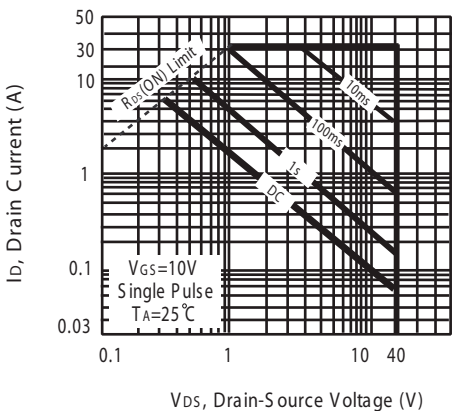
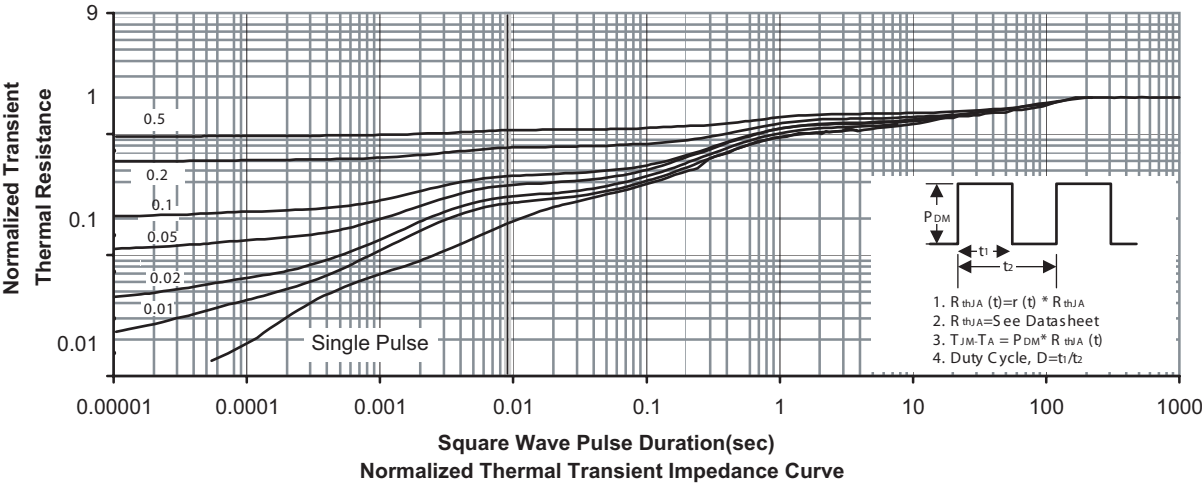


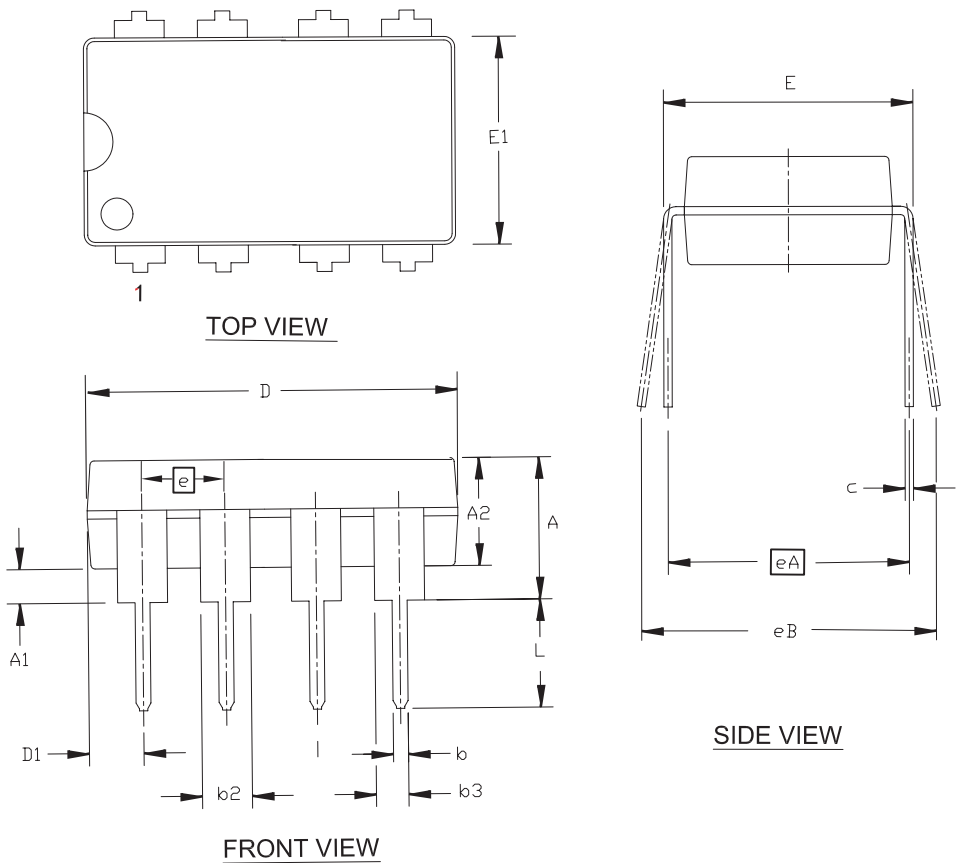
Figure 12. Maximum Safe Operating Area



STA6620

PACKAGE OUTLINE DIMENSIONS

PDIP 8



SYMBOL	INCHES			MILLIMETERS		
	MIN	NOM	MAX	MIN	NOM	MAX
A	.145	.172	.200	3.68	4.37	5.08
A1	.020	-	-	0.51	-	-
A2	.125	.130	.135	3.18	3.30	3.43
b	.015	.018	.021	0.38	0.46	0.53
c	.009	.012	.014	0.23	0.30	0.36
b2	.045	.060	.070	1.14	1.52	1.78
b3	.030	.039	.045	0.76	0.99	1.14
L	.125	.132	.140	3.18	3.35	3.56
e	.090	.100	.110	2.29	2.54	2.79
D	.373	.386	.400	9.47	9.80	10.16
D1	.030	.045	.060	0.76	1.14	1.52
E	.300	.310	.320	7.62	7.87	8.13
E1	.245	.250	.255	6.22	6.35	6.48
eA	.280	-	-	7.11	-	-
eB	.310	.325	.365	7.87	8.26	9.27